

## ABSTRACT OF THE DISCLOSURE

The invention includes selective oxidation methods and transistor fabrication methods. In one implementation, a selective oxidation method includes positioning a substrate within a chamber. The substrate has first and second different oxidizable materials. The substrate is therein exposed to a gas mixture comprising an oxidizer and a reducer under conditions effective to selectively grow an oxide layer on the first material relative to the second material. The oxidizer oxidizes the first and second materials under the conditions. The reducer reduces oxidized second material under the conditions back to the second material. After selectively growing the oxide layer on the first material relative to the second material, partial pressure of the oxidizer and the reducer is reduced within the chamber by flowing an inert gas to the chamber while chamber pressure and chamber temperature are at or above those of the conditions during the exposing. Other aspects and implementations are contemplated.